

## HIGH-VOLTAGE HIGH-CURRENT DARLINGTON TRANSISTOR ARRAYS

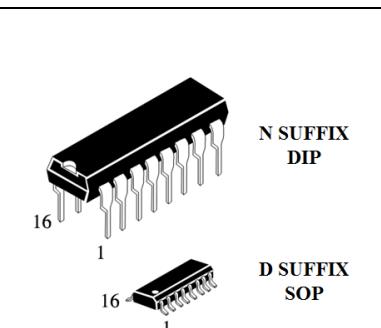
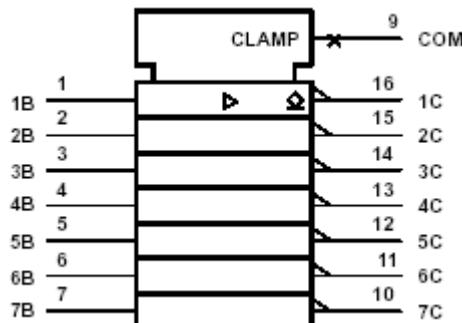
ILN2003A

The ILN2003A are monolithic high-voltage, high-current Darlington transistor arrays. Each consists of seven n-p-n Darlington pairs that feature high-voltage outputs with common-cathode clamp diodes for switching inductive loads. The collector-current rating of a single Darlington pair is 500 mA. The Darlington pairs may be paralleled for higher current capability. Applications include relay drivers, hammer drivers, lamp drivers, display drivers (LED and gas discharge), line drivers, and logic buffers.

The ILN2003A has a 2.7-k $\Omega$  series base resistor for each Darlington pair for operation directly with TTL or 5-V CMOS devices.

- 500-mA Rated Collector Current (Single Output)
- High-Voltage Outputs . . . 50 V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic
- Relay Driver Applications

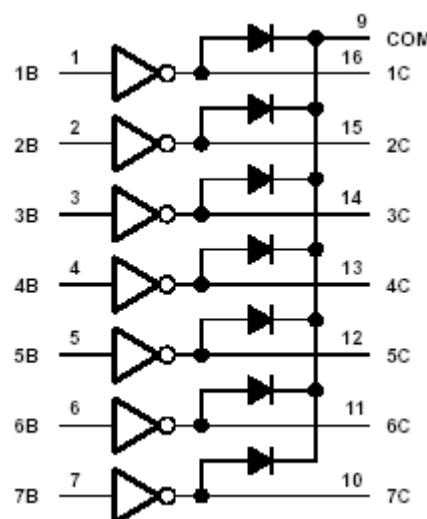
### LOGIC SYMBOL



### ORDERING INFORMATION

ILN2003AN	DIP
ILN2003ADT	SOP
$T_A = -40^\circ\text{C}$ to $85^\circ\text{C}$ for all packages	

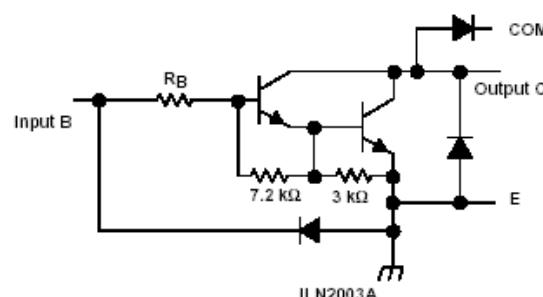
### LOGIC DIAGRAM



### SCHEMATICS (each Darlington Pair)

All resistor values shown are nominal.

**ILN2003A:  $R_B = 2.7\text{ k}\Omega$**



## Absolute Maximum Ratings (Ta =25°C)

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Output Sustaining Voltage	V <sub>CE(SUS)</sub>	-0.5	50	V
Output Current	I <sub>OUT</sub>	500		mA/ch
Input Voltage	V <sub>IN</sub>	-0.5	30	V
Clamp Diode Reverse Voltage	V <sub>R</sub>	50		V
Clamp Diode Forward Current	I <sub>F</sub>	500		mA
Power Dissipation	DIP	1.15		W
	SOP	0.95		
Operating Temperature	T <sub>opr</sub>	-40	85	°C
Storage Temperature	T <sub>stg</sub>	-55	150	°C

\* Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## Recommended Operating Conditions (Ta= -40~85°C)

Parameter	Symbol	Test Condition	Limit Value			Unit
			Min	Typ	Max	
Output Sustaining Voltage	V <sub>CE(SUS)</sub>		0	-	50	V
Output Current	I <sub>OUT</sub>	T <sub>pw</sub> =25ms,Duty=10%, 7 Circuits	0	-	370	mA/ch
		T <sub>pw</sub> =25ms,Duty=30%, 7 Circuits	0	-	200	
		T <sub>pw</sub> =25ms,Duty=10%, 7 Circuits	0	-	290	
		T <sub>pw</sub> =25ms,Duty=30%, 7 Circuits	0	-	150	
Input Voltage	V <sub>IN</sub>		0	-	30	V
Clamp Diode Reverse Voltage	V <sub>R</sub>		-	-	50	V
Clamp Diode Forward Current	I <sub>F</sub>		-	-	400	mA
Power Dissipation	DIP		-	-	0.52	W
	SOP		-	-	0.4	

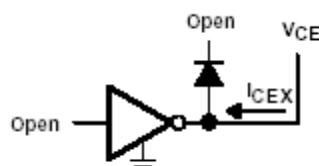
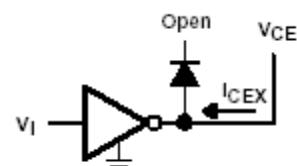
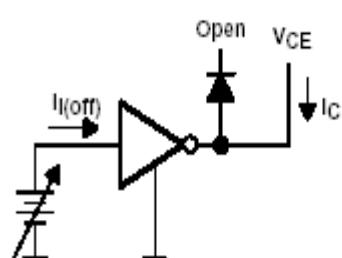
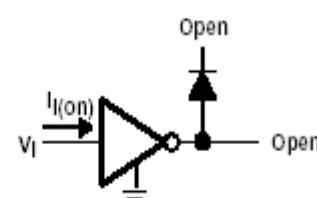
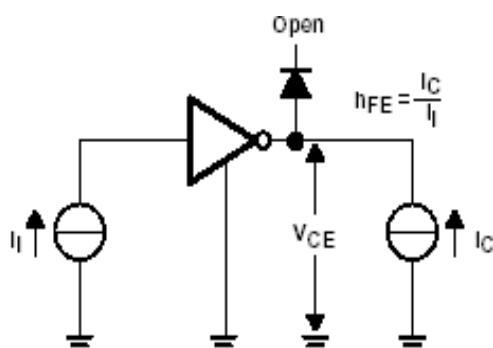
**Electrical characteristics,  $T_A = 25^\circ\text{C}$  (unless otherwise noted)**

Parameter	Test Fig.	Test Conditions		Min	Typ	Max	Unit
$V_{I(on)}$ On-state Input Voltage	6	$V_{CE}=2\text{V}$	$I_C=125\text{mA}$				V
			$I_C=200\text{mA}$			2.4	
			$I_C=250\text{mA}$			2.7	
			$I_C=275\text{mA}$				
			$I_C=300\text{mA}$			3	
			$I_C=350\text{mA}$				
$V_{CE(sat)}$ Collector-emitter saturation voltage	5	$I_I=250\mu\text{A}$	$I_C=100\text{mA}$		0.9	1.1	V
		$I_I=350\mu\text{A}$	$I_C=200\text{mA}$		1	1.3	
		$I_I=500\mu\text{A}$	$I_C=350\text{mA}$		1.2	1.6	
$I_{CEX}$ Collector outoff current	1	$V_{CE}=50\text{V}$	$I_I=0$			50	uA
	2	$V_{CE}=50\text{V}, T_A=85^\circ\text{C}$	$I_I=0$			100	
$h_{FE}$ DC Current Transfer Ratio	5	$V_{CE}=2\text{V}, I_{OUT}=350\text{mA}$		1000	-	-	
$V_F$ Clamp forward voltage	8	$I_F=350\text{mA}$			1.7	2	V
$I_{I(off)}$ Off-state input current	3	$V_{CE}=50\text{V}$	$I_C=500\mu\text{A}$	50	65		uA
$I_I$ Input current	4	$V_I=2.4\text{V}$			0.4	0.7	mA
		$V_I=5\text{V}$					
		$V_I=12\text{V}$					
$I_R$ Clamp reverse current	7	$V_R=50\text{V}$				50	uA
		$V_R=50\text{V}$	$T_A=85^\circ\text{C}$			100	
$C_I$ Input capacitance		$V_I=0$	$f=1\text{MHz}$		15	25	pF

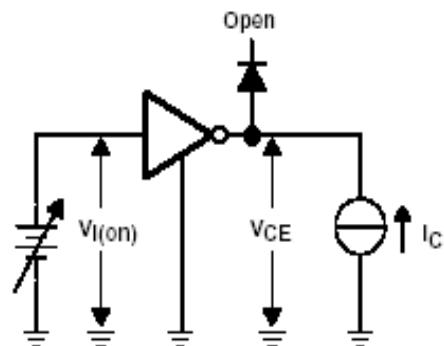
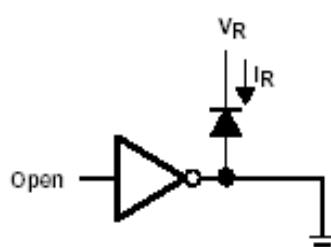
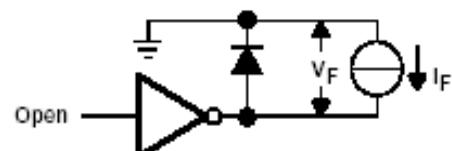
**Switching Characteristics,  $T_A=25^\circ\text{C}$** 

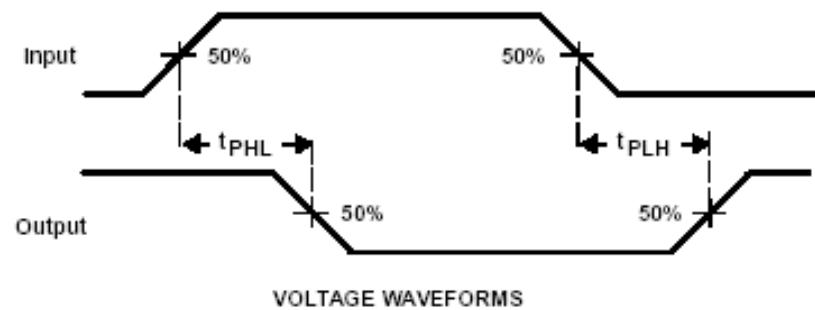
Parameter	Test Conditions	Min	Typ	Max	Unit
$t_{PLH}$ Propagation delay time, low-to-high-level output	See Figure 9		0.25	1	us
$t_{PHL}$ Propagation delay time, high -to- low -level output			0.25	1	us
$V_{OH}$ High-level output voltage after switching	$V_S=50\text{V}, I_O=300\text{mA},$ See Figure 10	$V_S-20$			mV

## PARAMETER MEASUREMENT INFORMATION

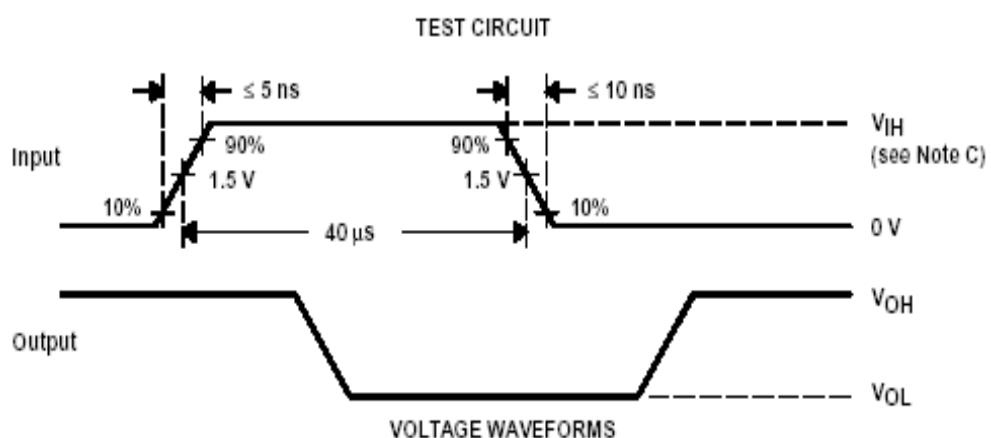
Figure 1.  $I_{CEx}$  Test CircuitFigure 2.  $I_{CEx}$  Test CircuitFigure 3.  $I_{I(off)}$  Test CircuitFigure 4.  $I_I$  Test Circuit

NOTE:  $I_I$  is fixed for measuring  $V_{CE(sat)}$ , variable for measuring  $hFE$ .

Figure 5.  $hFE$ ,  $V_{CE(sat)}$  Test CircuitFigure 6.  $V_{I(on)}$  Test CircuitFigure 7.  $I_R$  Test CircuitFigure 8.  $V_F$  Test Circuit



**Figure 9. Propagation Delay-Time Waveforms**



NOTES: A. The pulse generator has the following characteristics: PRR = 12.5 kHz,  $Z_0 = 50 \Omega$ .

B.  $C_L$  includes probe and jig capacitance.

C.  $V_{IH} = 3$  V;

**Figure 10. Latch-Up Test Circuit and Voltage Waveforms**

## TYPICAL CHARACTERISTICS

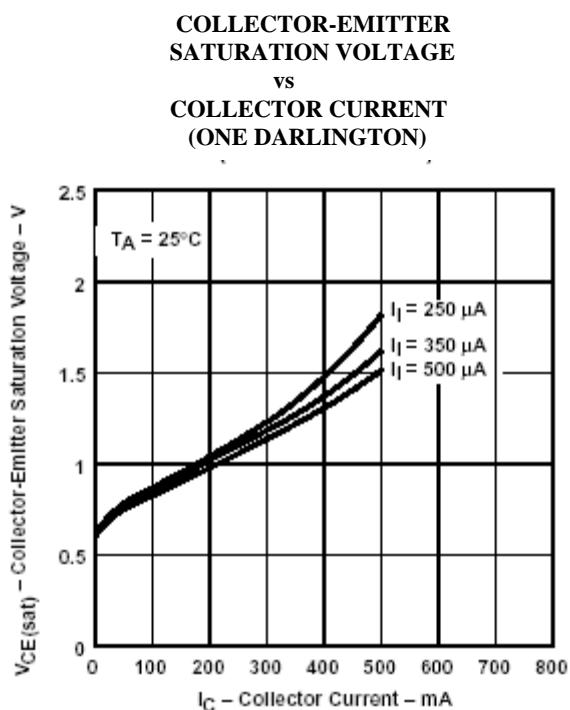


Figure 11

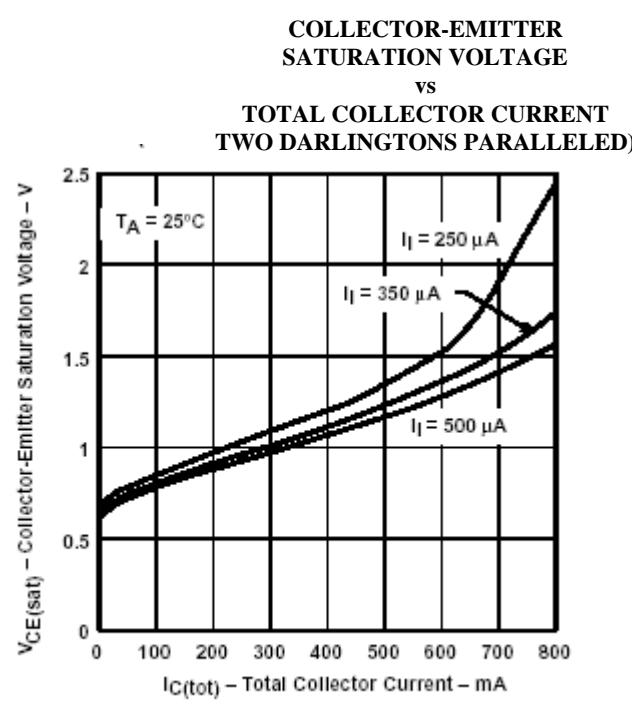


Figure 12

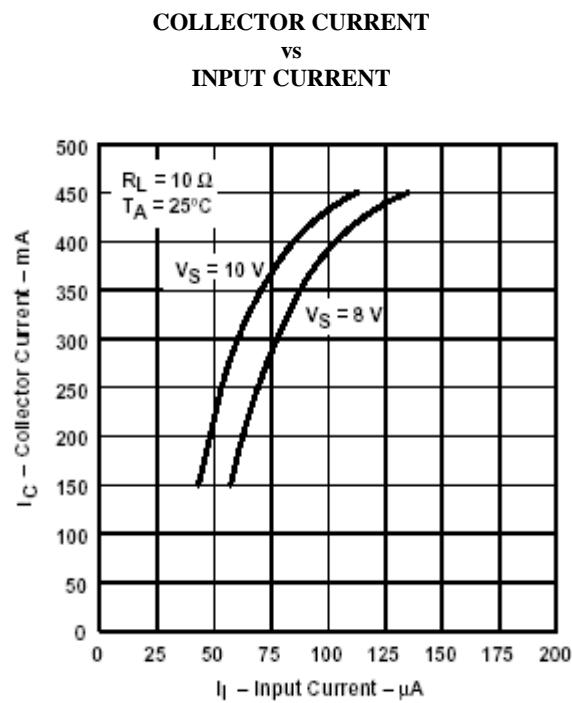


Figure 13

## THERMAL INFORMATION

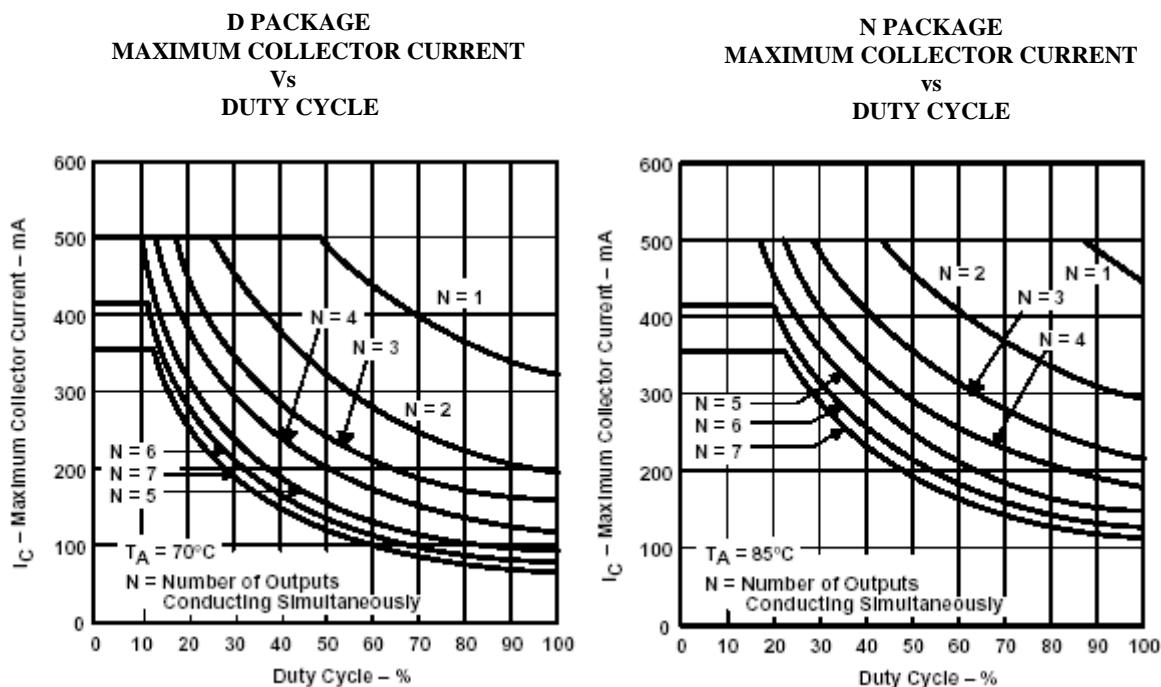
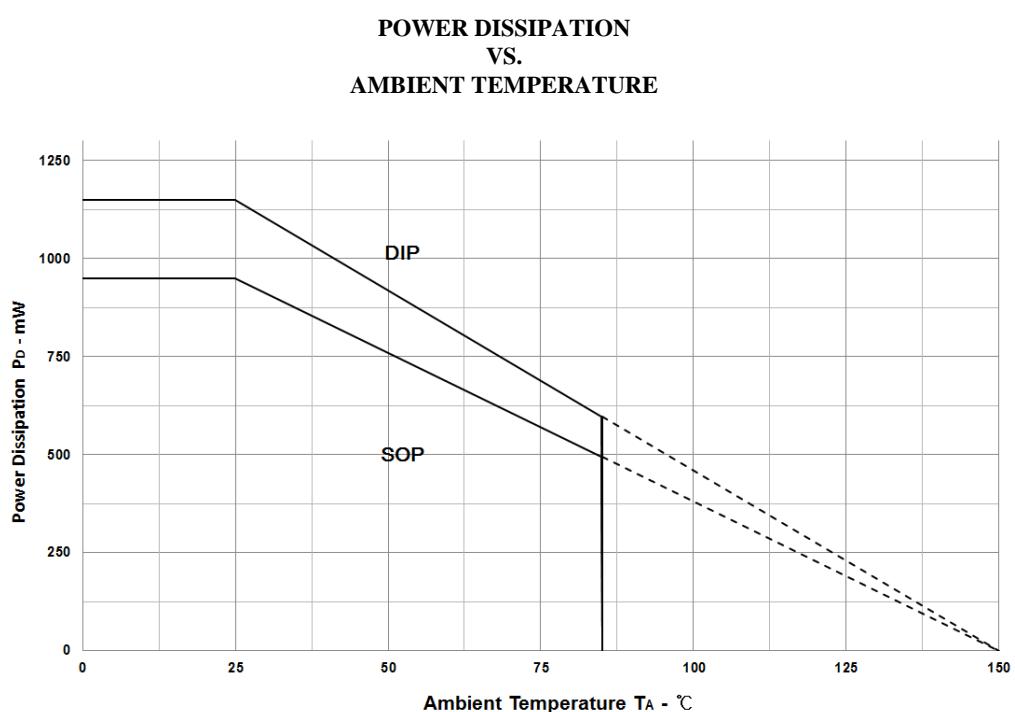


Figure 14

Figure 15



## APPLICATION INFORMATION

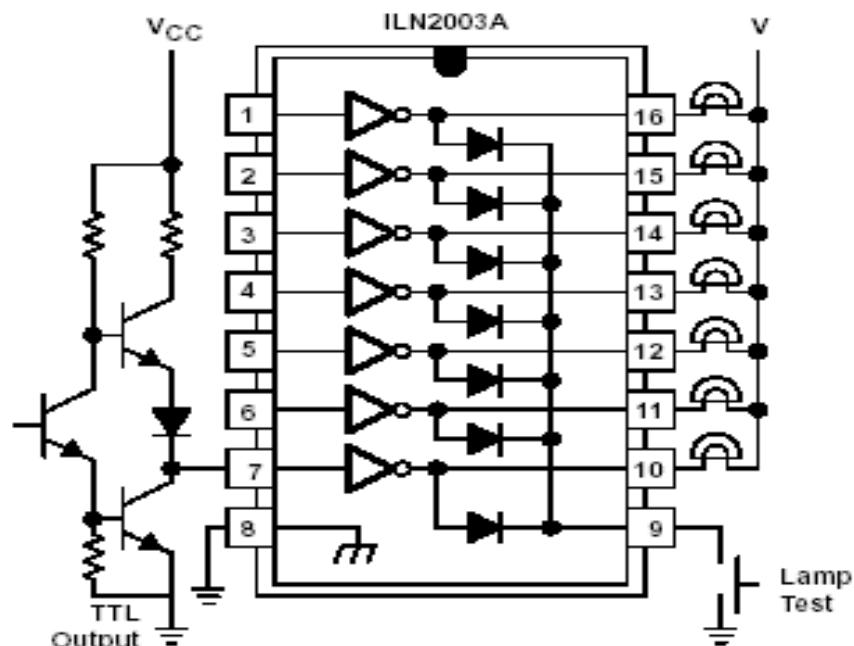


Figure 16. TTL to Load

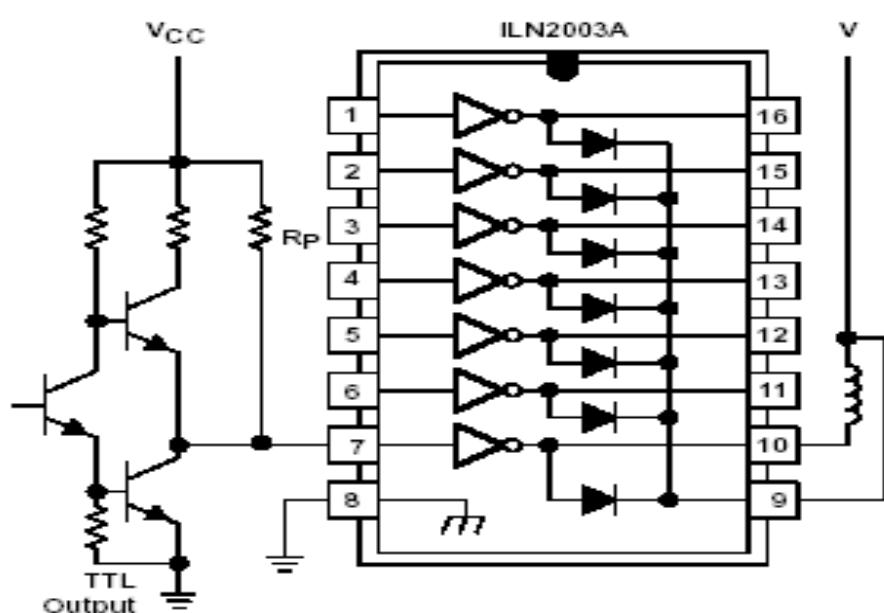
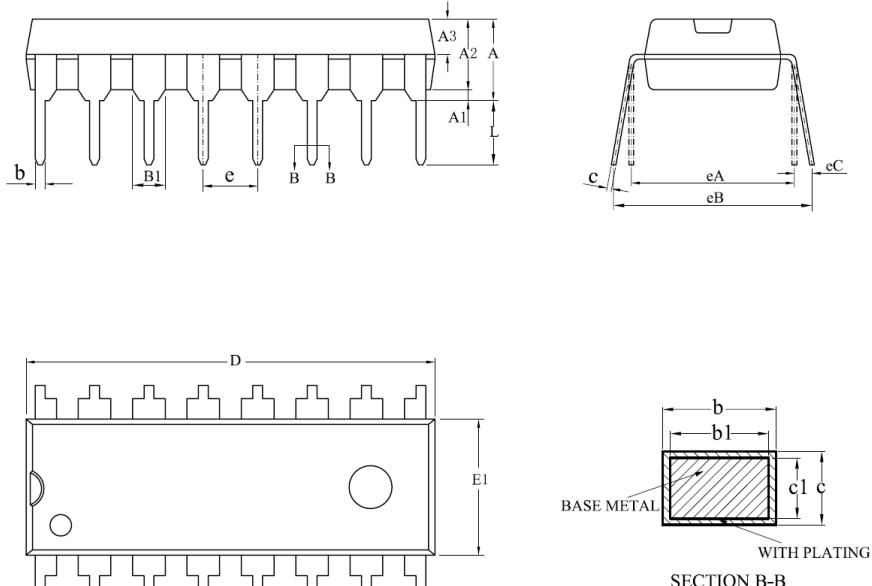


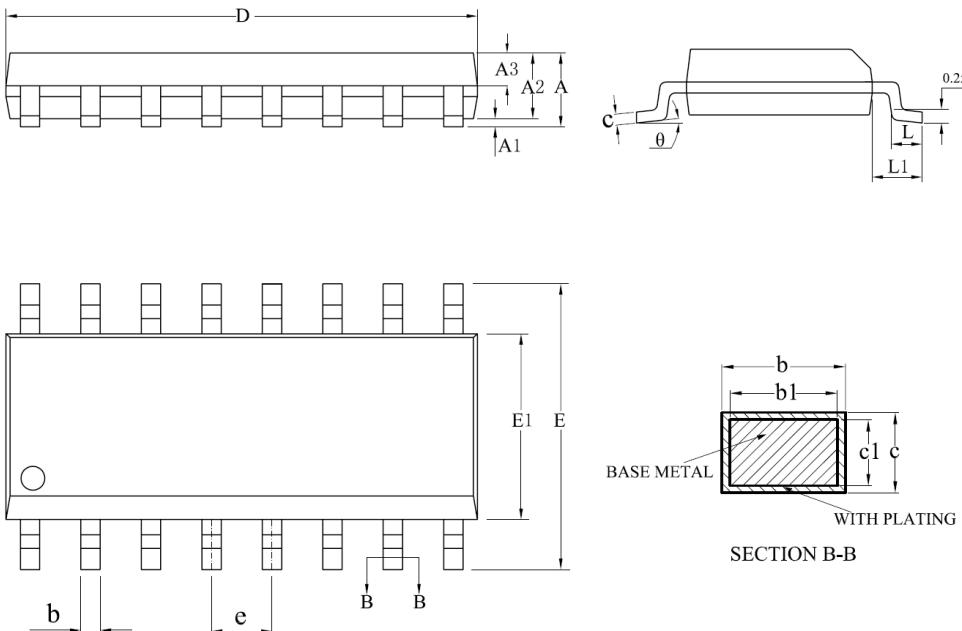
Figure 17. Use of Pullup Resistors to Increase Drive Current

## DIP-16



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	3.60	3.80	4.00
A1	0.51	—	—
A2	3.10	3.30	3.50
A3	1.42	1.52	1.62
b	0.44	—	0.53
b1	0.43	0.46	0.48
B1	1.52BSC		
c	0.25	—	0.31
c1	0.24	0.25	0.26
D	18.90	19.10	19.30
E1	6.15	6.35	6.55
e	2.54BSC		
eA	7.62BSC		
eB	7.62	—	9.50
eC	0	—	0.94
L	3.00	—	—
L/F载体尺寸 (mil)			80*80
			110*140
			140*170

## SOP-16



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	—	—	1.75
A1	0.10	—	0.25
A2	1.35	1.40	1.45
A3	0.60	0.65	0.70
b	0.39	—	0.48
b1	0.38	0.41	0.43
c	0.21	—	0.26
c1	0.19	0.20	0.21
D	9.70	9.90	10.10
E	5.80	6.00	6.20
E1	3.70	3.90	4.10
e	1.27BSC		
L	0.50	—	0.80
L1	1.05BSC		
θ	0	—	8°
L/F载体尺寸 (mil)			75*75
			90*110
			90*180